

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

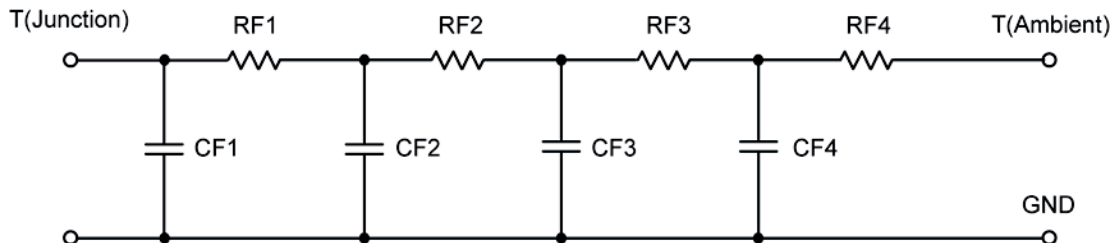
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	29.8920	N/A	10.8326
RT2	9.6346	N/A	2.2792
RT3	23.3151	N/A	11.1761
RT4	46.8127	N/A	7.7180
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	16.1452 m	N/A	6.8156 m
CT2	3.1375 m	N/A	1.2824 m
CT3	216.5650 m	N/A	40.0156 m
CT4	1.7119	N/A	181.3532 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	14.1037	N/A	3.2033
RF2	30.5460	N/A	15.8798
RF3	25.4384	N/A	9.7243
RF4	39.5492	N/A	3.1295
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	2.7352 m	N/A	891.4830 u
CF2	13.5454 m	N/A	5.4964 m
CF3	211.1310 m	N/A	50.5411 m
CF4	1.8029	N/A	181.5262 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

